

Silicon PNP Power Transistors

2SA1120

DESCRIPTION

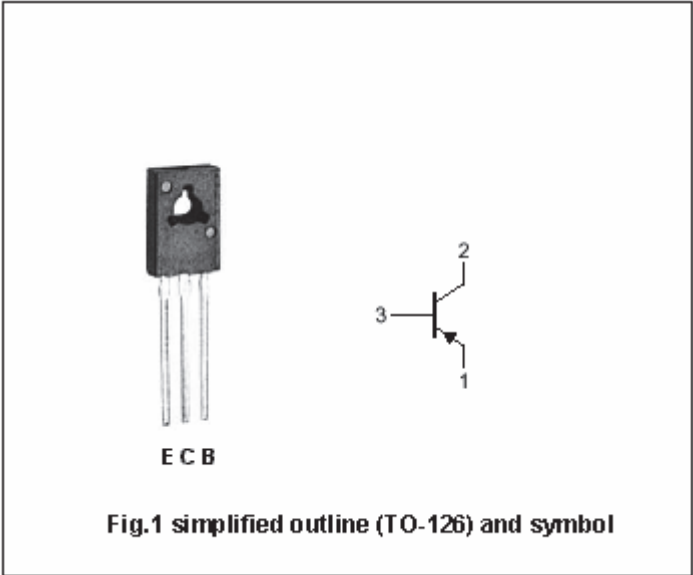
- With TO-126 package
- High transition frequency
- Low collector saturation voltage

APPLICATIONS

- Audio power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-35	V
V _{CEO}	Collector-emitter voltage	Open base	-35	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-5	A
I _B	Base current		-1	A
P _D	Total power dissipation	T _a =25℃	1.5	W
		T _C =25℃	5	
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-55~+150	℃

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA ; I _B =0	-35			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-4A; I _B =-0.1A			-1.0	V
V _{BE}	Base-emitter on voltage	I _C =-4A ; V _{CE} =-2V			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-35V; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-6V; I _C =0			-0.1	mA
h _{FE-1}	DC current gain	I _C =-500mA ; V _{CE} =-2V	200			
h _{FE-2}	DC current gain	I _C =-4A ; V _{CE} =-2V	70			
C _{ob}	Output capacitance	I _E =0 ; V _{CB} =-10V f=1MHz		62		pF
f _T	Transition frequency	I _C =-500mA ; V _{CE} =-2V		170		MHz

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PACKAGE OUTLINE

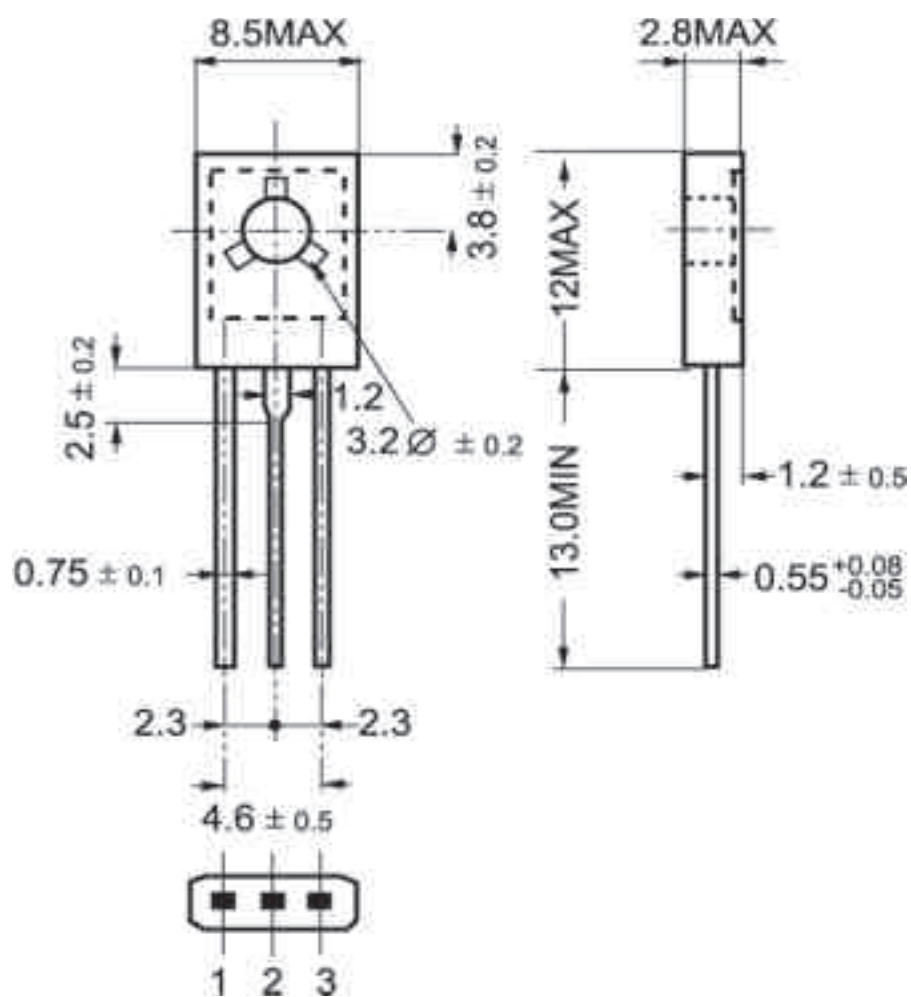


Fig.2 Outline dimensions